

N-Channel 30 V (D-S) Super Junction MOSFET

PRODUCT SUMMARY			
V _{DS} (V)	R _{DS(on)} (mΩ)(Typ.)	I _D (A) ^a	Q _g (Typ.)
30	1 at V _{GS} = 10 V	139	52 nC
	1.9 at V _{GS} = 4.5 V		

FEATURES

- DT-SJ Power MOSFET
- 100 % R_g and UIS Tested



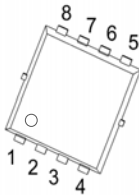
RoHS
COMPLIANT

APPLICATIONS

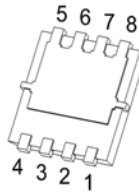
- Li- Battery Protection
- Motor Drive
- Power Management for High Performance Application

PDFN 3.3x3.3

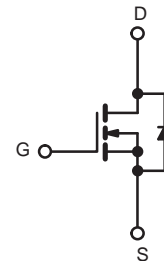
Top View



Bottom View



Top View



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C, unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	30	V
Gate-Source Voltage	V _{GS}	± 20	
Continuous Drain Current (T _J = 150 °C)	T _C = 25 °C	139	A
	T _C = 100 °C	88	
Pulsed Drain Current	I _{DM}	555	
Single-Pulse Avalanche Energy	E _{AS}	336	mJ
Maximum Power Dissipation	T _C = 25 °C	42	W
	T _C = 100 °C	16.8	
	T _A = 25 °C	2.5 ^{b,c}	
	T _A = 100 °C	1.0 ^{b,c}	
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to 150	°C

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^b	R _{thJA}	40	50	°C/W
Maximum Junction-to-Case	R _{thJC}	2.3	2.97	

Notes:

- a. Based on T_C = 25 °C.
 b. Surface mounted on 1" x 1" FR4 board.
 c. t = 10 s.

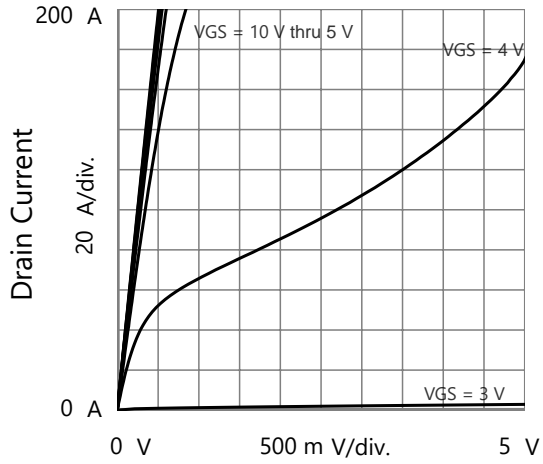
SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0, I_D = 250\text{ }\mu\text{A}$	30			V
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	1		3	V
Gate-Source Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}$			1	μA
		$V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$			100	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \geq 5\text{ V}, V_{GS} = 10\text{ V}$	139			A
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 20\text{ A}$		1	1.3	m Ω
		$V_{GS} = 4.5\text{ V}, I_D = 20\text{ A}$		1.9	2.6	
Forward Transconductance ^a	g_{fs}	$V_{DS} = 5\text{ V}, I_D = 20\text{ A}$		40		S
Dynamic^b						
Input Capacitance	C_{iss}	$V_{DS} = 15\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$		2990		pF
Output Capacitance	C_{oss}			2040		
Reverse Transfer Capacitance	C_{rss}			74		
Total Gate Charge	Q_g	$V_{DS} = 15\text{ V}, V_{GS} = 10\text{ V}, I_D = 20\text{ A}$		52		nC
Gate-Source Charge	Q_{gs}			7.1		
Gate-Drain Charge	Q_{gd}			11		
Gate Resistance	R_g	$f = 1\text{ MHz}$		1.8		Ω
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 15\text{ V}, R_L = 0.5\text{ }\Omega$ $I_D \cong 20\text{ A}, V_{GEN} = 10\text{ V}, R_g = 3\text{ }\Omega$		7		ns
Rise Time	t_r			30		
Turn-Off Delay Time	$t_{d(off)}$			34		
Fall Time	t_f			22		
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	$T_C = 25\text{ }^\circ\text{C}$			139	A
Pulse Diode Forward Current (100 μs)	I_{SM}				555	
Body Diode Voltage	V_{SD}	$I_S = 1\text{ A}$			1.2	V
Body Diode Reverse Recovery Time	t_{rr}	$I_F = 20\text{ A}, dI/dt = 100\text{ A}/\mu\text{s}, T_J = 25\text{ }^\circ\text{C}$		49		ns
Body Diode Reverse Recovery Charge	Q_{rr}				58	

Notes:

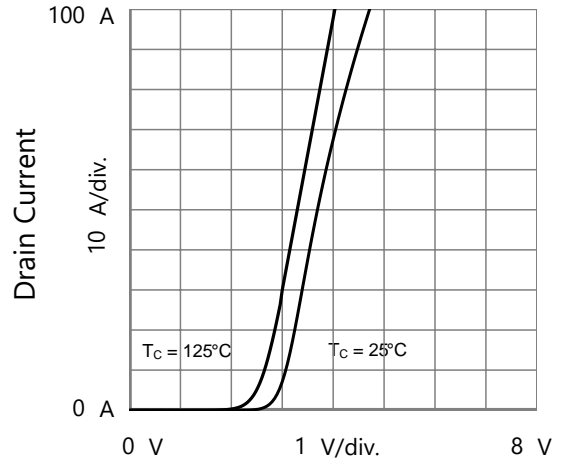
- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
 b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

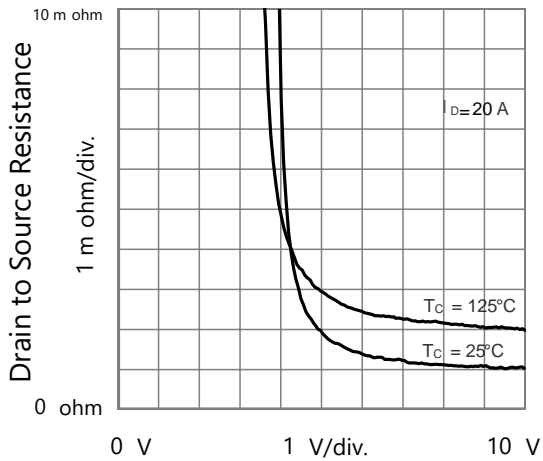
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



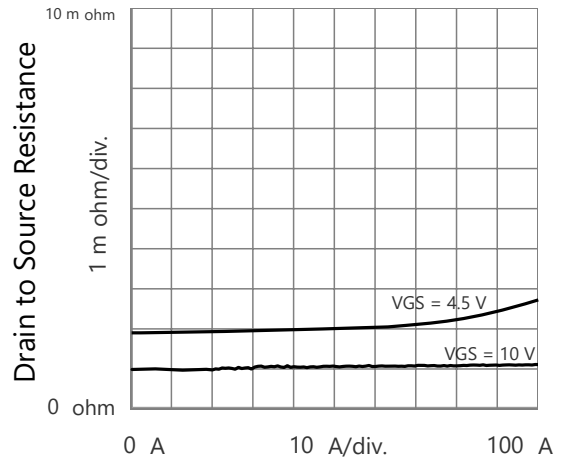
Drain to Source Voltage
Output Characteristics



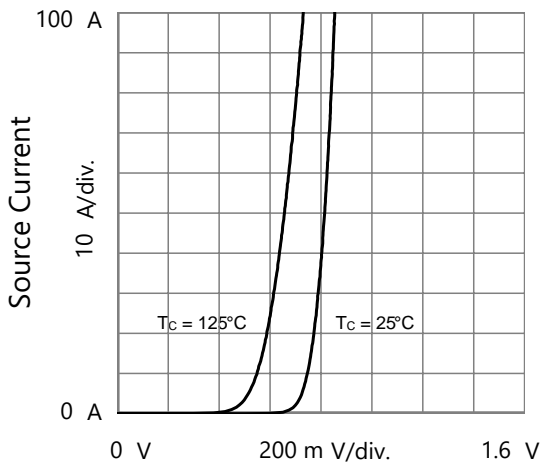
Gate to Source Voltage
Transfer Characteristics



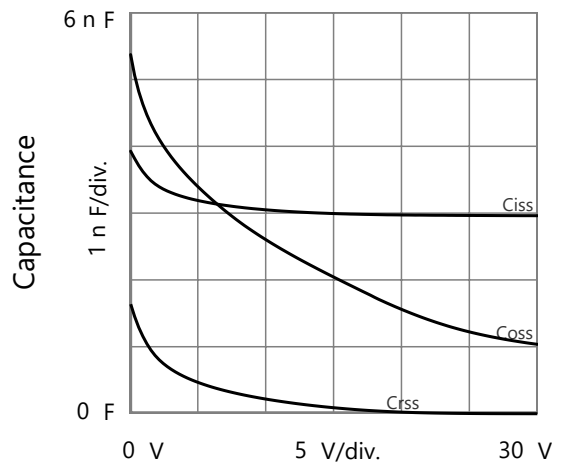
Gate to Source Voltage
Drain to Source Resistance vs. Gate to Source Voltage



Drain Current
Drain to Source Resistance vs. Drain Current

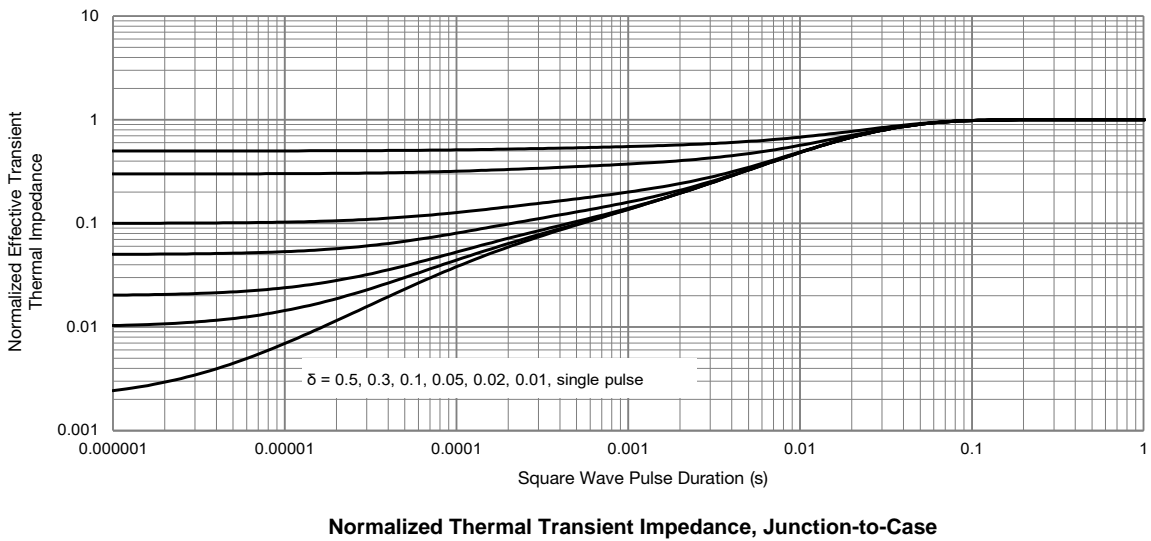
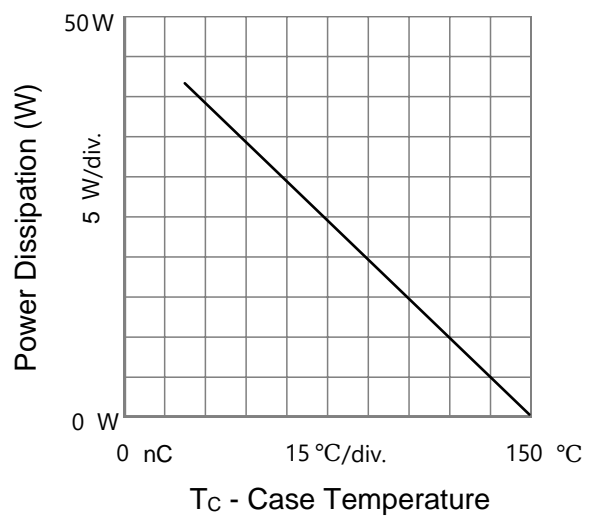
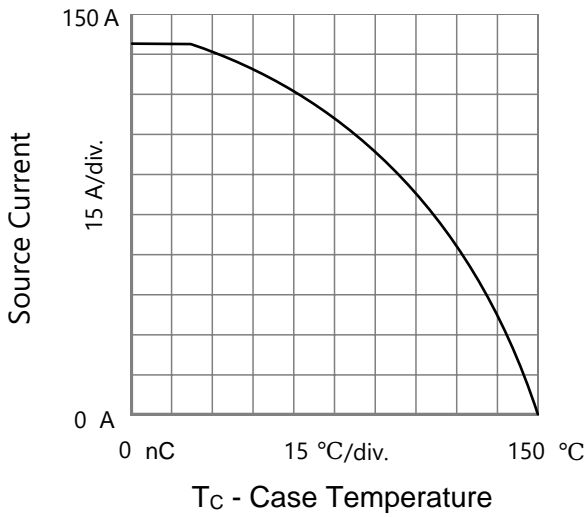
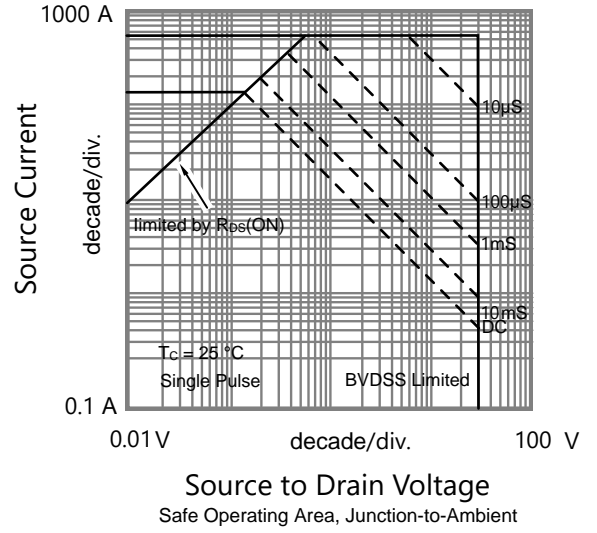
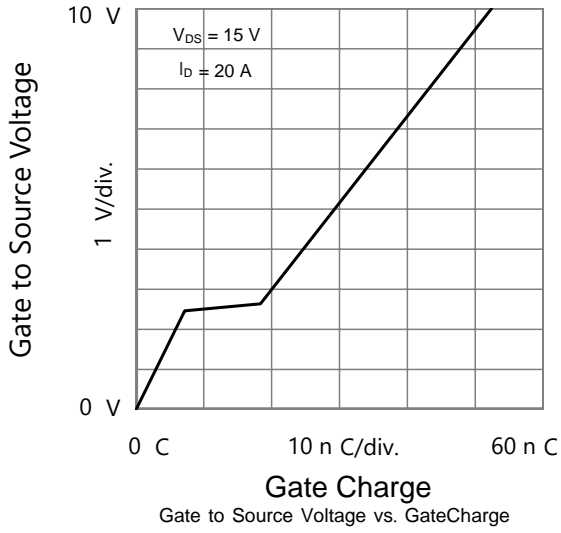


Source to Drain Voltage
Body Diode Forward Characteristics



Drain to Source Voltage
Capacitances

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



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